TGA2622-CP

9 – 10 GHz 35 W GaN Power Amplifier

Product Description

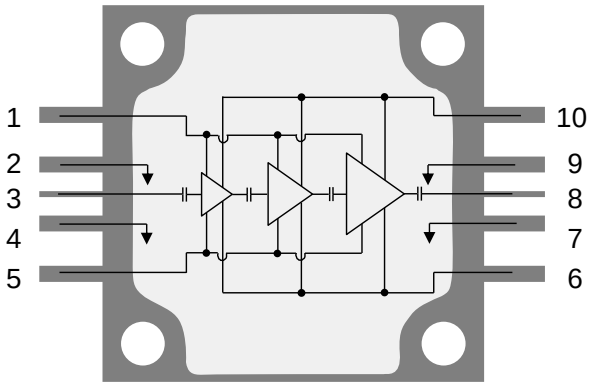
Qorvo's TGA2622-CP is a packaged high-power X-Band amplifier fabricated on Qorvo's QGaN25 0.25 um GaN on SiC process. Operating from 9 to 10 GHz, the TGA2622-CP achieves 35 W saturated output power, a power-added efficiency of greater than 43 %, and power gain of 27.5 dB.

The TGA2622-CP is packaged in a 10-lead 15x15 mm bolt-down package with a Cu base for superior thermal management. It can support a range of bias voltages and performs well under CW and pulsed conditions. Both RF ports are internally DC blocked and matched to 50 ohms allowing for simple system integration.

The TGA2622-CP is ideally suited for both commercial and defense applications.

Lead free and RoHS compliant.

Functional Block Diagram



Product Features

- Frequency Range: 9 – 10 GHz
- P_{SAT}: 45.5 dBm @ P_{IN} = 18 dBm
- PAE: > 43 % @ P_{IN} = 18 dBm
- Power Gain: 27.5 dB @ P_{IN} = 18 dBm
- Bias: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical, pulsed (PW = 100 µs, DC = 10 %)
- Package Dimensions: 15.2 x 15.2 x 3.5 mm
- Package base is pure Cu offering superior thermal management

Performance is typical across frequency. Please reference electrical specification table and data plots for more details

Applications

- Weather and Marine Radar.

Ordering Information

Part No.	Description
TGA2622-CP	9 – 10 GHz 35 W GaN Power Amplifier
1113526	TGA2622-CP Evaluation Board (EVB)

Absolute Maximum Ratings

Parameter	Value / Range
Drain Voltage (V_D)	40 V
Gate Voltage Range (V_G)	-8 to 0 V
Drain Current (I_D)	4.3 A
Gate Current (I_G)	See plot page 11
Power Dissipation (P_{DISS}), 85 °C	107 W
Input Power, CW, 50 Ω, (P_{IN})	24 dBm
Input Power, CW, VSWR 3:1, V_D = 28 V, 85 °C, (P_{IN})	24 dBm
Mounting Temperature (30 Seconds)	260 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

Recommended Operating Conditions

Parameter	Value / Range
Drain Voltage (V_D) pulsed: PW = 100 µs, DC = 10 %	28 V
Drain Current (I_{DQ})	290 mA
Gate Voltage (V_G)	−2.7 V (Typ.)
Temperature (T_{BASE})	-40 to 85 °C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications

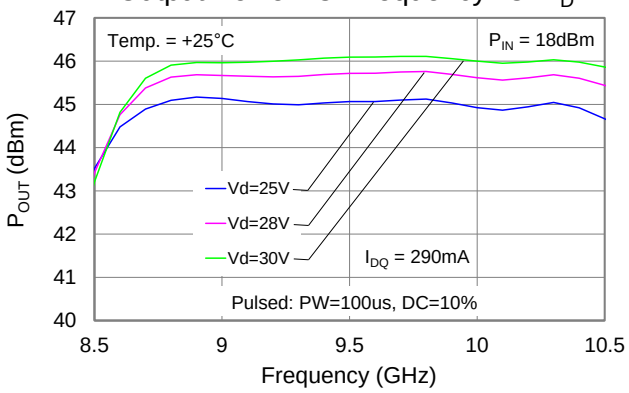
Parameter		Min	Typ	Max	Units
Operational Frequency Range		9		10	GHz
Small Signal Gain			30		dB
Input Return Loss			> 11		dB
Output Return Loss			> 8		dB
Output Power @ P_{IN} = 18 dBm			45.5		dBm
Power Added Efficiency @ P_{IN} = 18 dBm			> 43		%
Power Gain @ P_{IN} = 18 dBm			27.5		dB
Output Power Temperature Coefficient (25 °C to 85 °C only)	Pulsed		-0.019		dBm/°C
	CW		-0.023		
Recommended Operating Voltage		20	28	32	V

Test conditions unless otherwise noted: 25 °C, V_D = 28 V (PW = 100 µs, DC = 10 %), I_{DQ} = 290 mA, V_G = -2.7 V typical.

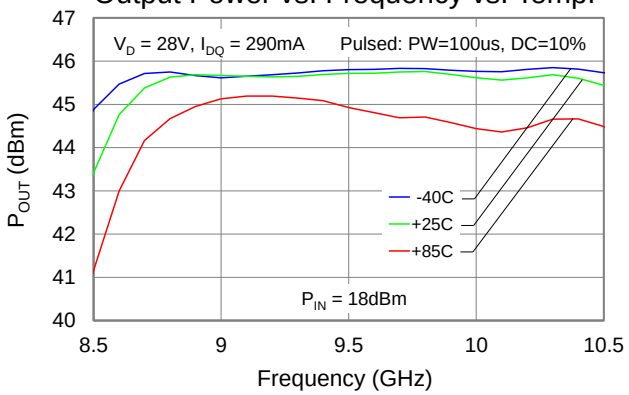
Typical Performance – Large Signal (Pulsed)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

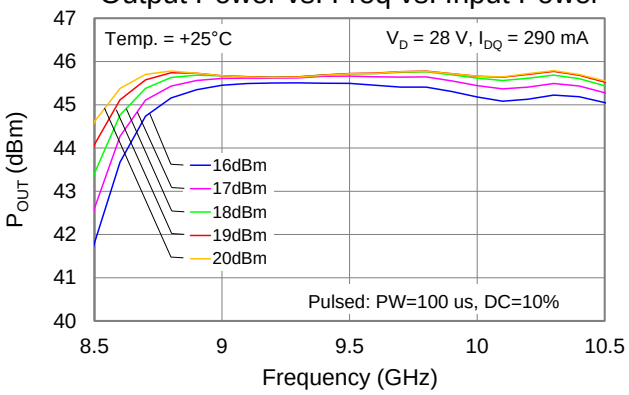
Output Power vs. Frequency vs. V_D



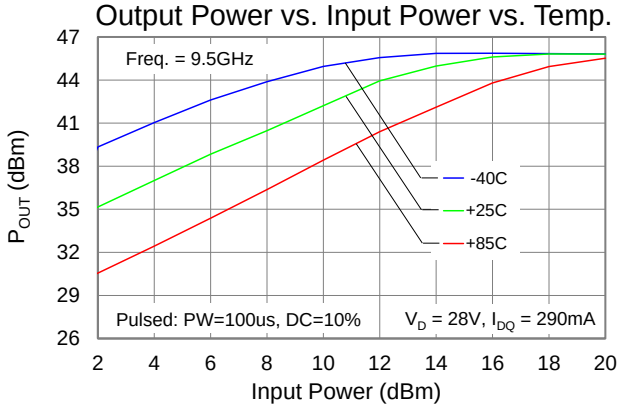
Output Power vs. Frequency vs. Temp.



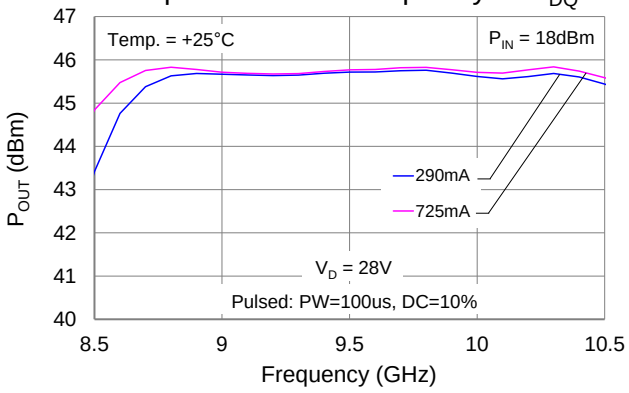
Output Power vs. Freq vs. Input Power



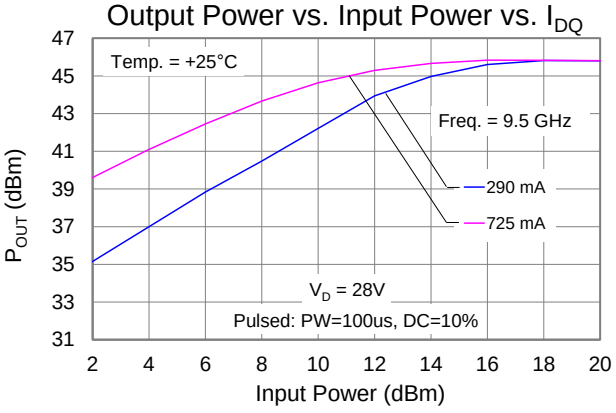
Output Power vs. Input Power vs. Temp.



Output Power vs. Frequency vs. I_{DQ}



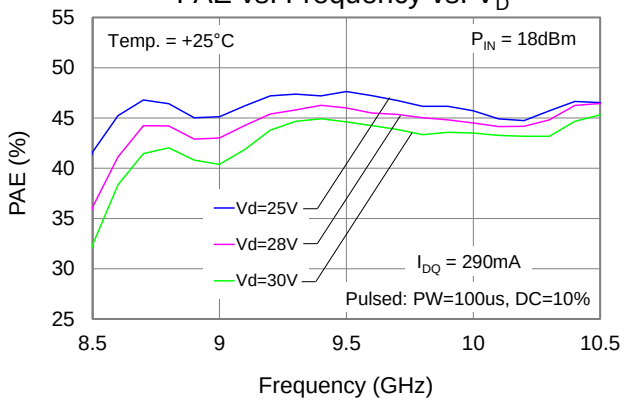
Output Power vs. Input Power vs. I_{DQ}



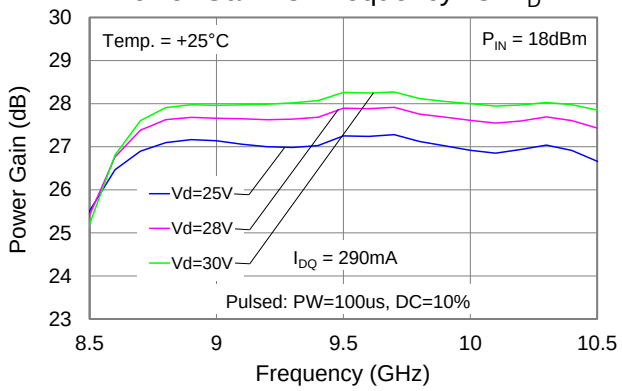
Typical Performance – Large Signal (Pulsed)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

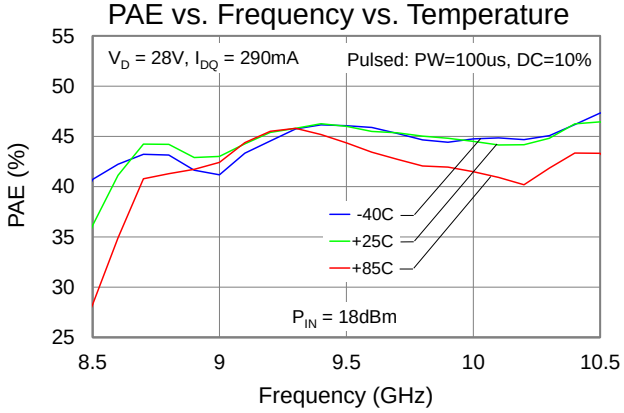
PAE vs. Frequency vs. V_D



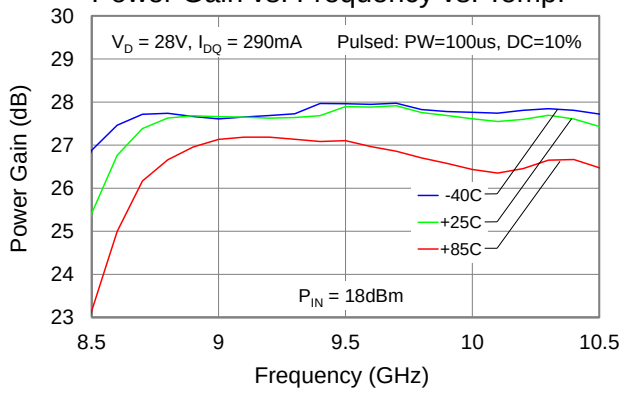
Power Gain vs. Frequency vs. V_D



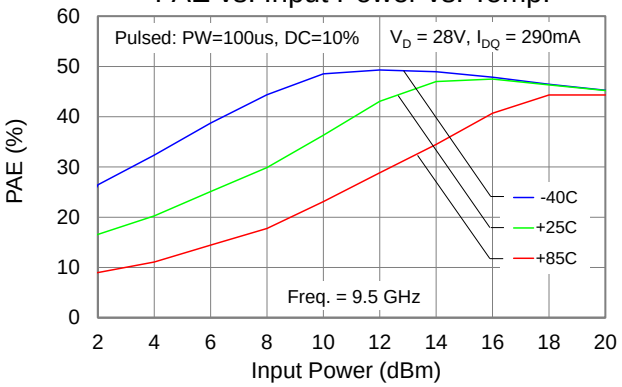
PAE vs. Frequency vs. Temperature



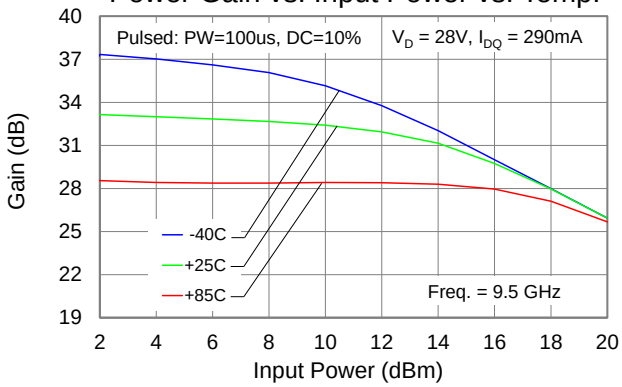
Power Gain vs. Frequency vs. Temp.



PAE vs. Input Power vs. Temp.



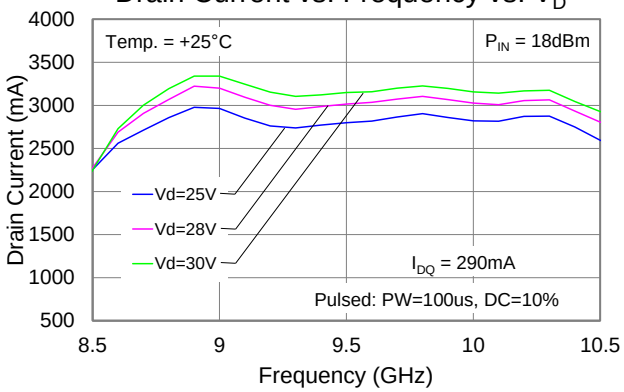
Power Gain vs. Input Power vs. Temp.



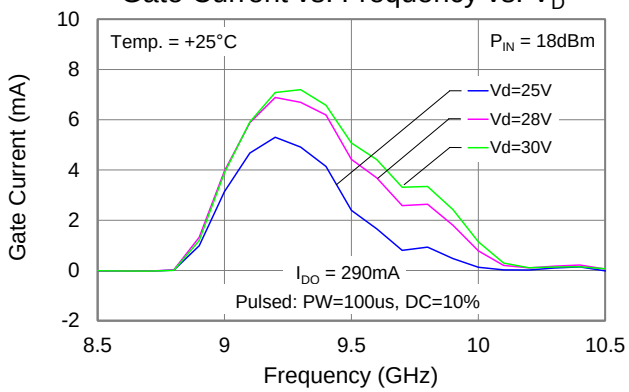
Typical Performance – Large Signal (Pulsed)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

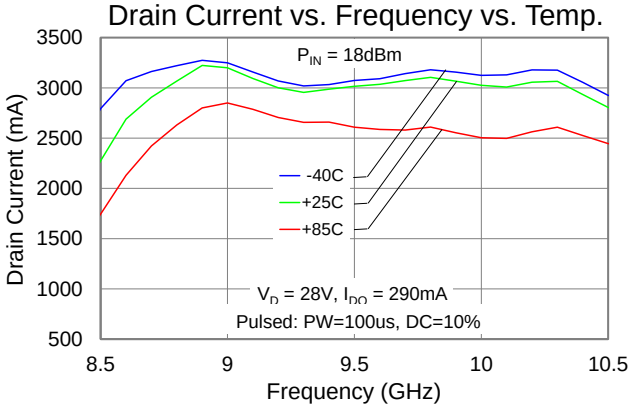
Drain Current vs. Frequency vs. V_D



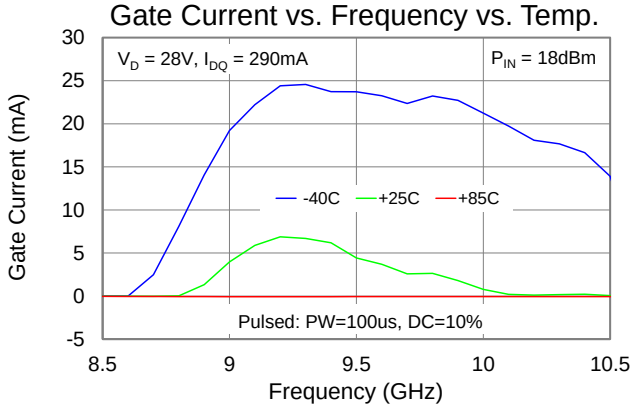
Gate Current vs. Frequency vs. V_D



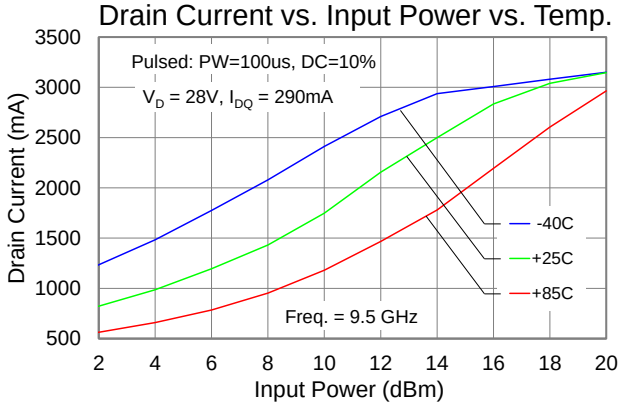
Drain Current vs. Frequency vs. Temp.



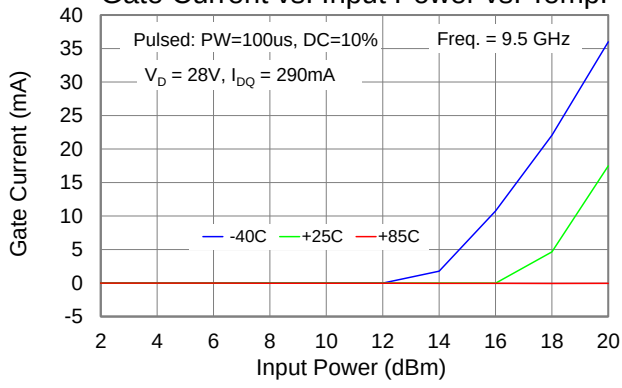
Gate Current vs. Frequency vs. Temp.



Drain Current vs. Input Power vs. Temp.



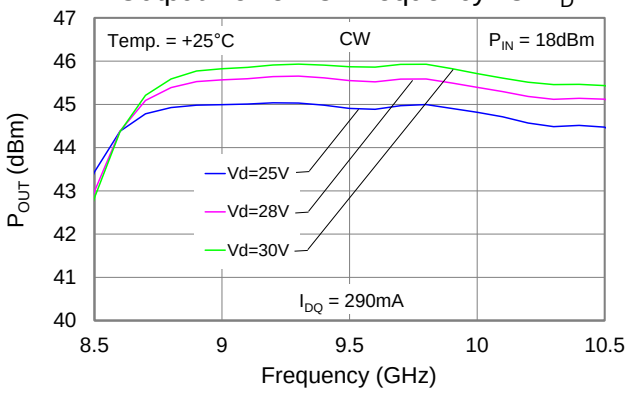
Gate Current vs. Input Power vs. Temp.



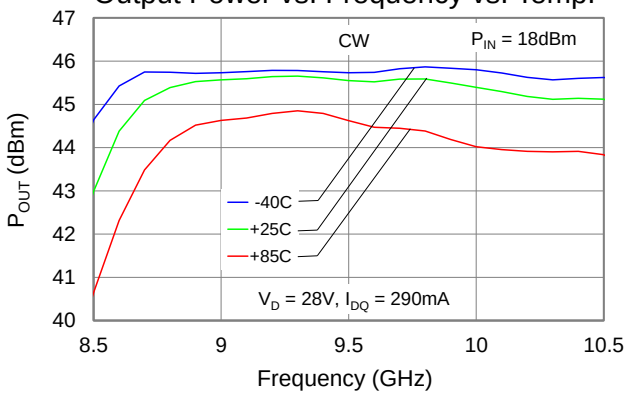
Performance Plots – Large Signal (CW)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

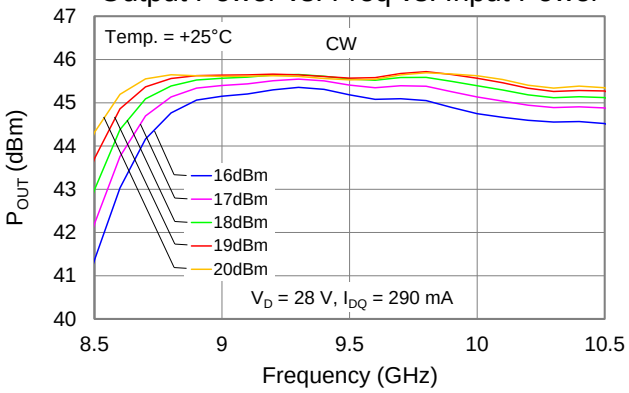
Output Power vs. Frequency vs. V_D



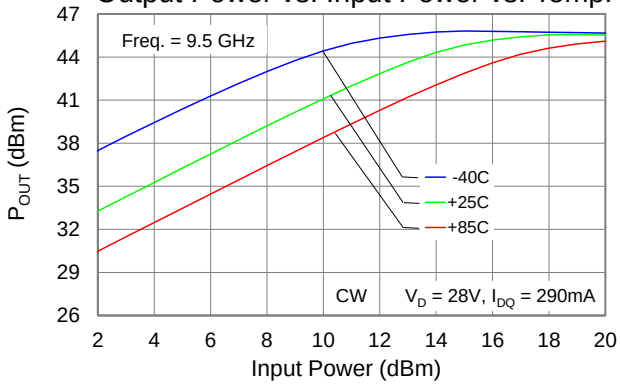
Output Power vs. Frequency vs. Temp.



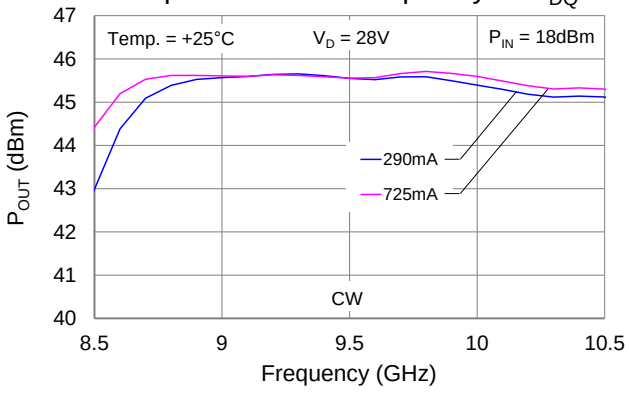
Output Power vs. Freq vs. Input Power



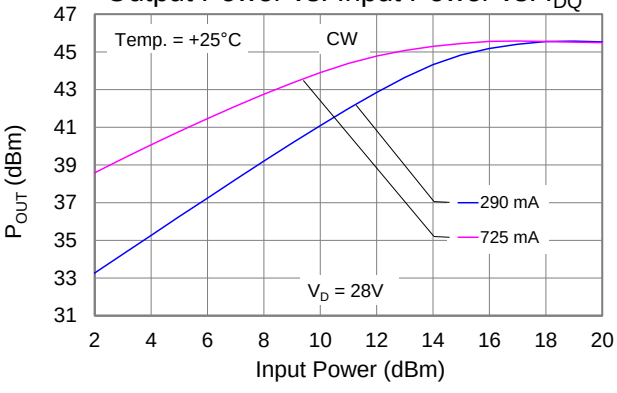
Output Power vs. Input Power vs. Temp.



Output Power vs. Frequency vs. I_{DQ}



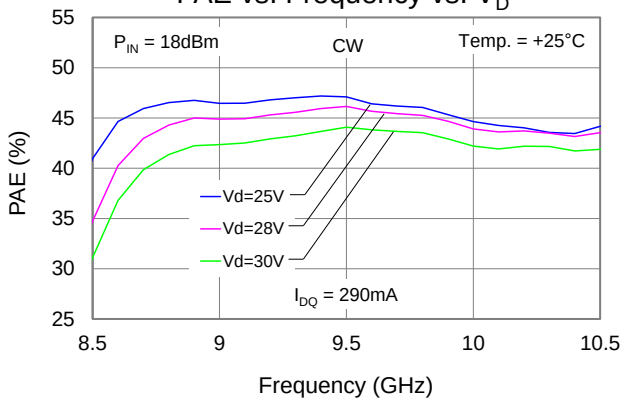
Output Power vs. Input Power vs. I_{DQ}



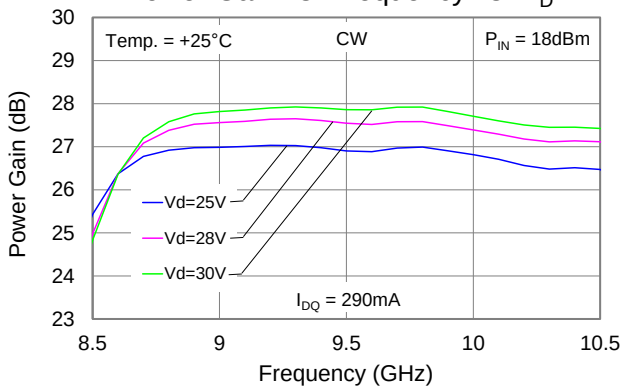
Performance Plots – Large Signal (CW)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

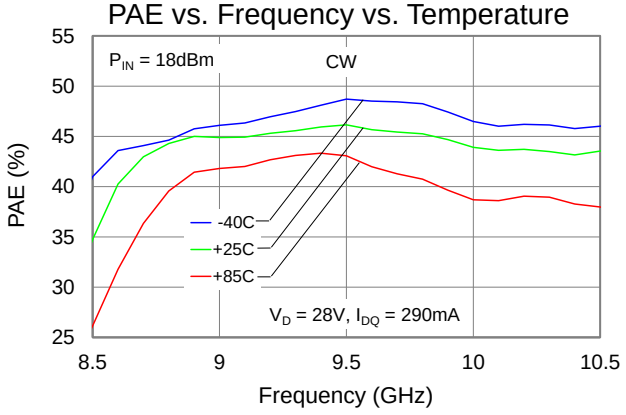
PAE vs. Frequency vs. V_D



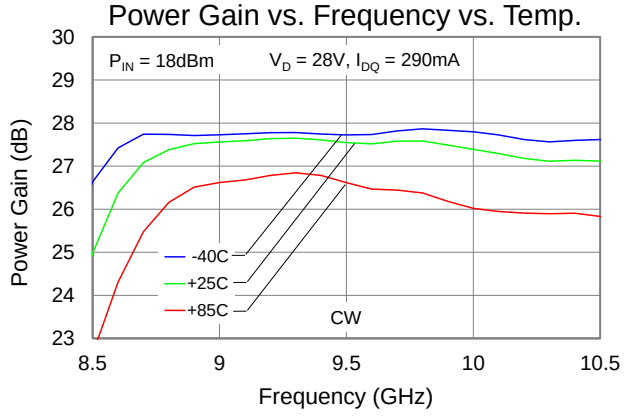
Power Gain vs. Frequency vs. V_D



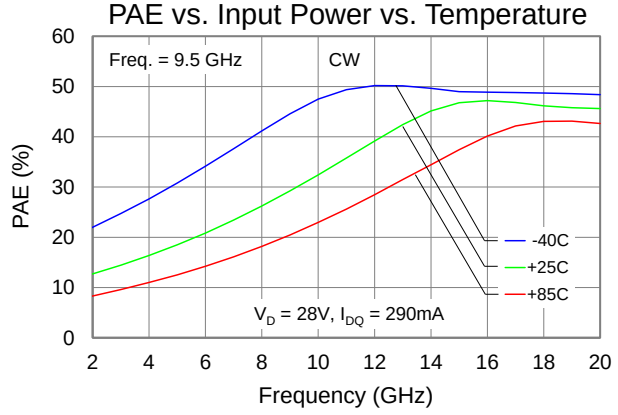
PAE vs. Frequency vs. Temperature



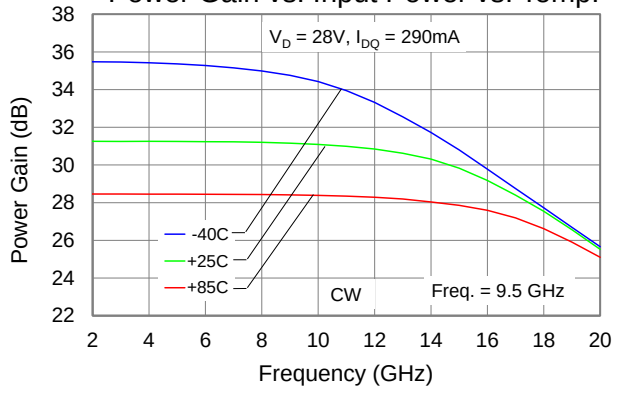
Power Gain vs. Frequency vs. Temp.



PAE vs. Input Power vs. Temperature



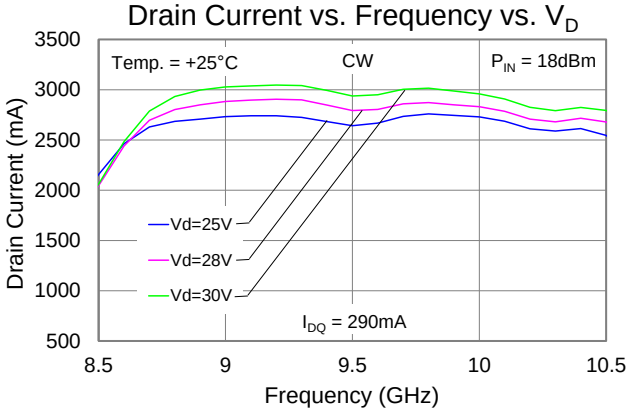
Power Gain vs. Input Power vs. Temp.



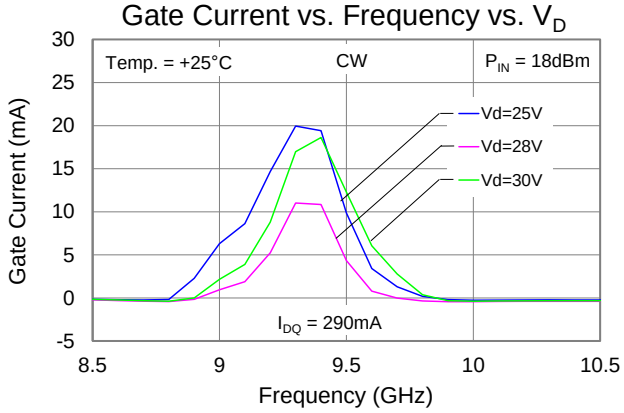
Performance Plots – Large Signal (CW)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

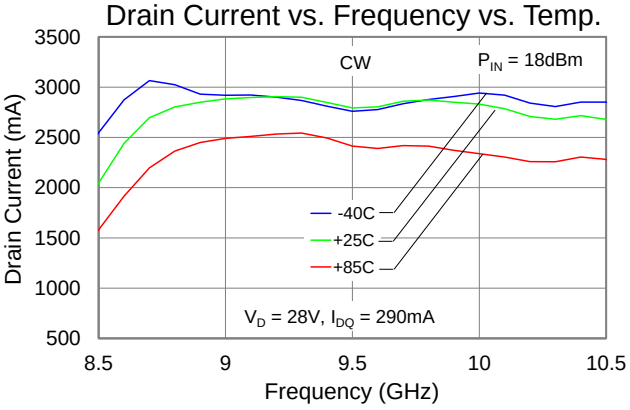
Drain Current vs. Frequency vs. V_D



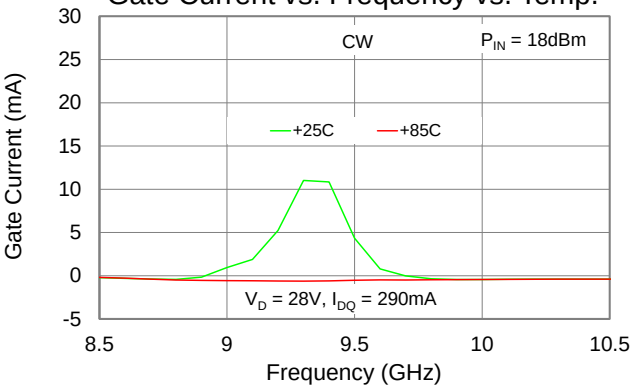
Gate Current vs. Frequency vs. V_D



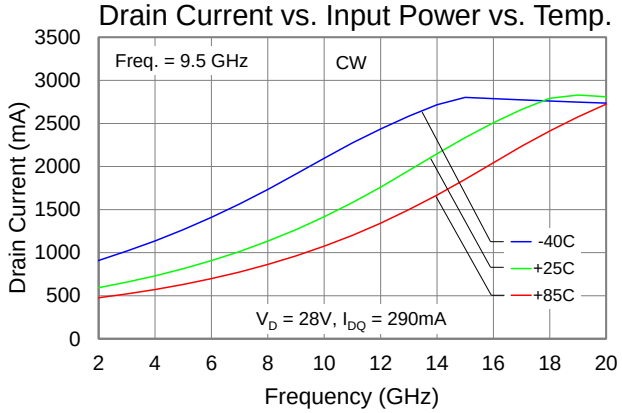
Drain Current vs. Frequency vs. Temp.



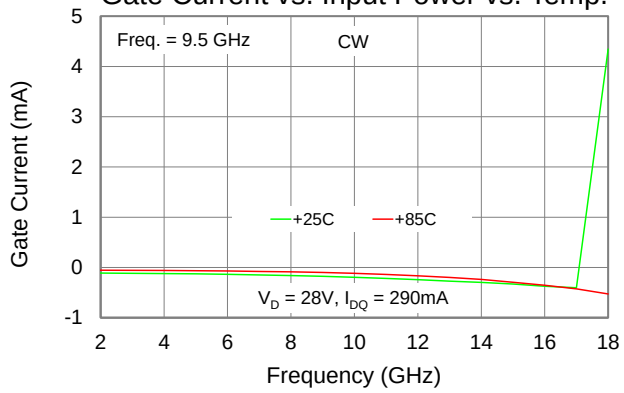
Gate Current vs. Frequency vs. Temp.



Drain Current vs. Input Power vs. Temp.



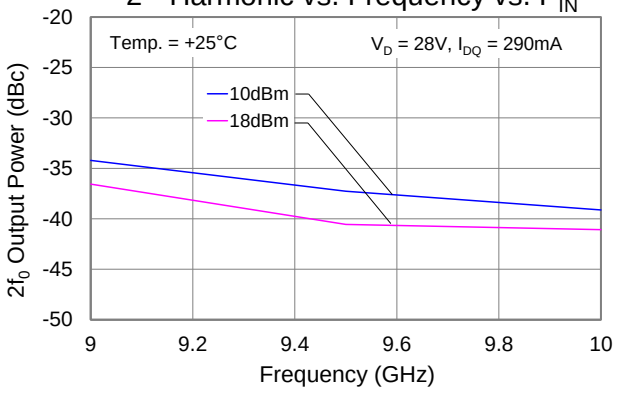
Gate Current vs. Input Power vs. Temp.



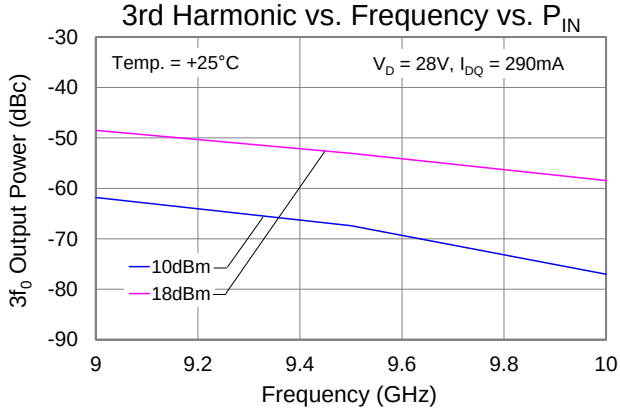
Typical Performance – Linearity (CW)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

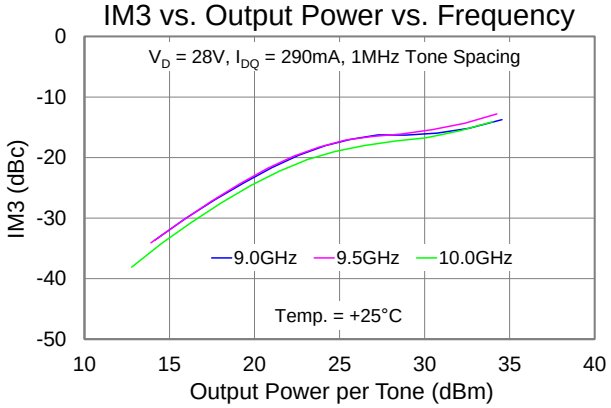
2nd Harmonic vs. Frequency vs. P_{IN}



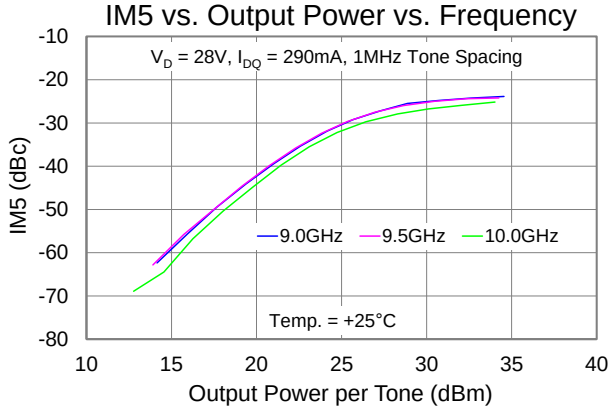
3rd Harmonic vs. Frequency vs. P_{IN}



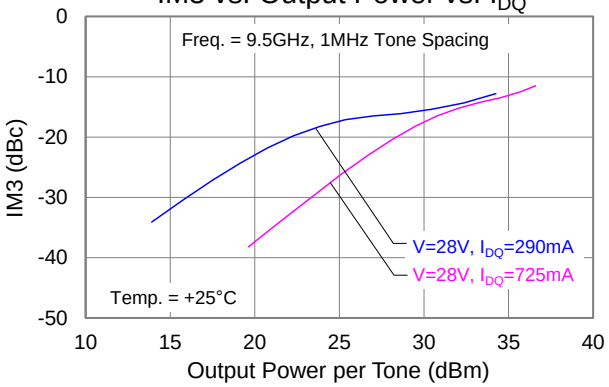
IM3 vs. Output Power vs. Frequency



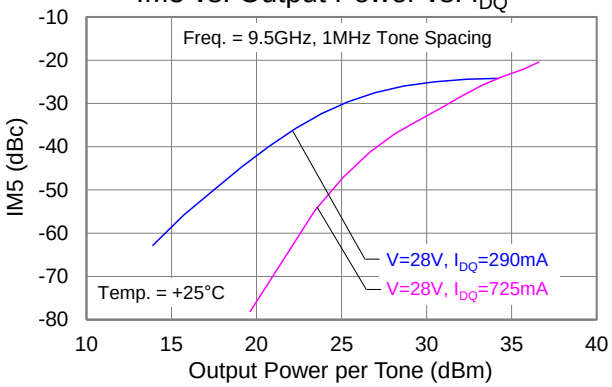
IM5 vs. Output Power vs. Frequency



IM3 vs. Output Power vs. I_{DQ}



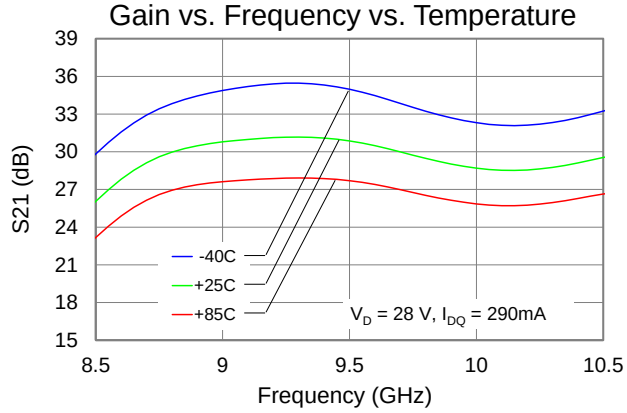
IM5 vs. Output Power vs. I_{DQ}



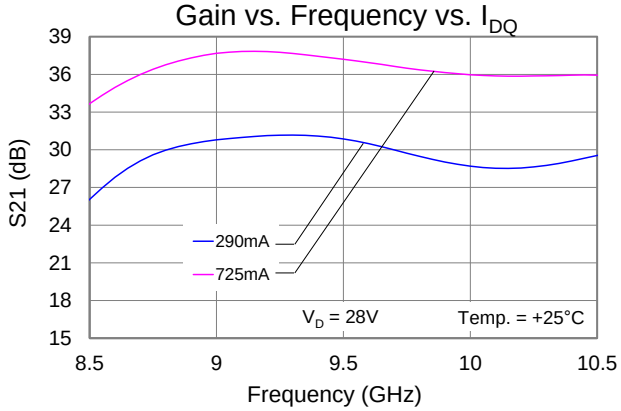
Typical Performance – Small Signal (CW)

Conditions unless otherwise specified: V_D = 28 V, I_{DQ} = 290 mA, V_G = -2.7 V typical.

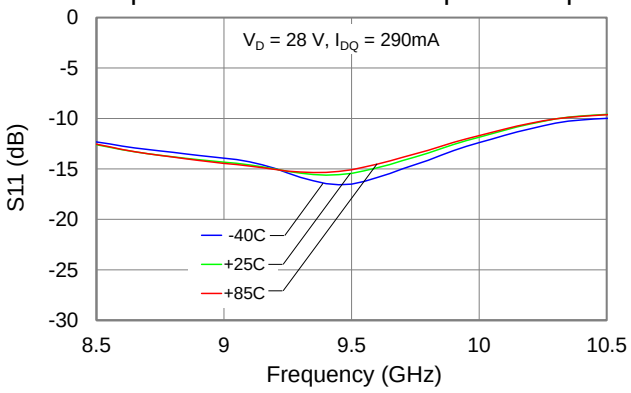
Gain vs. Frequency vs. Temperature



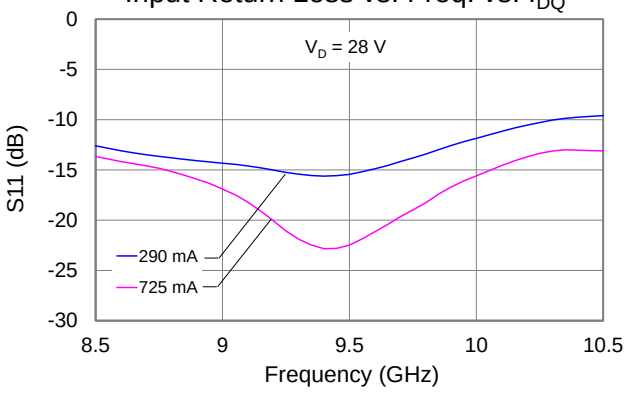
Gain vs. Frequency vs. I_{DQ}



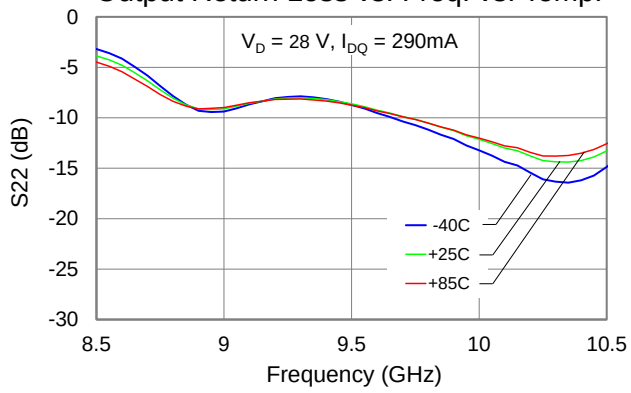
Input Return Loss vs. Freq. vs. Temp.



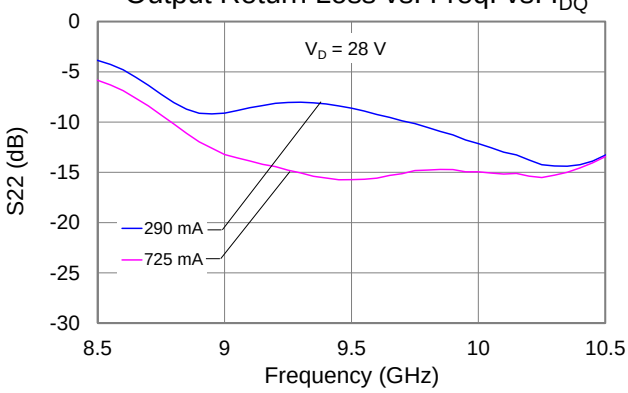
Input Return Loss vs. Freq. vs. I_{DQ}



Output Return Loss vs. Freq. vs. Temp.



Output Return Loss vs. Freq. vs. I_{DQ}

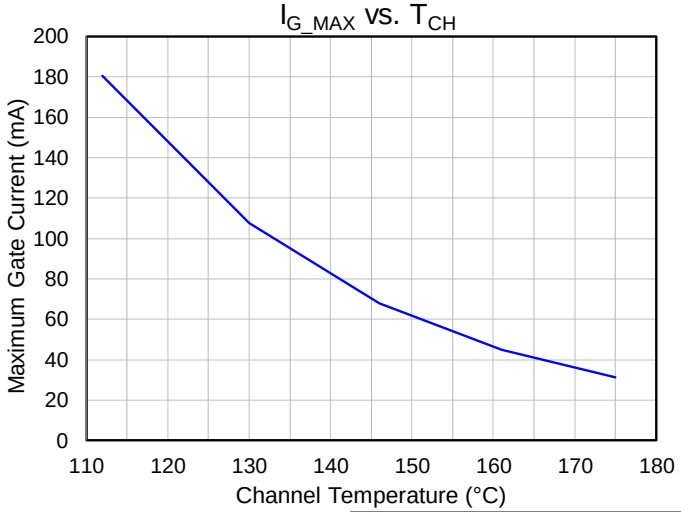


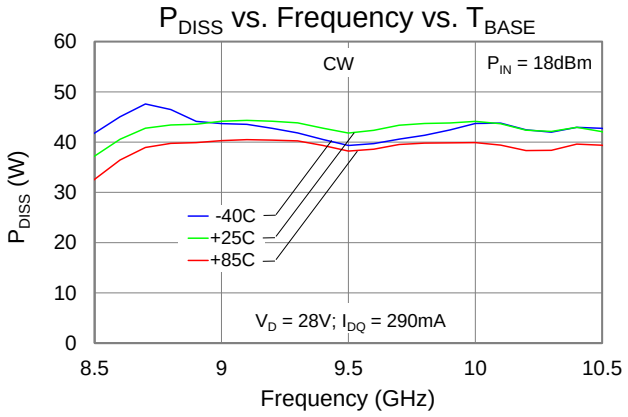
Thermal and Reliability Information

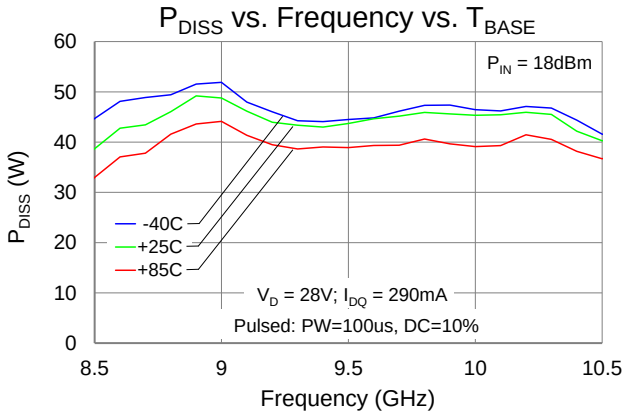
Parameter	Test Conditions	Value	Units
Thermal Resistance (θ_{JC}) (1)	CW, V_D = 28 V, I_{DQ} = 290 mA, T_{BASE} = 85°C, V_D = 28 V, I_{D_Drive} = 2.7 A P_{IN} = 20 dBm, P_{OUT} = 44.8 dBm P_{DISS} = 45 W	1.222	°C/W
Channel Temperature (T_{CH}) (under RF drive)		140	°C
Thermal Resistance (θ_{JC}) (1)	V_D = 28 V, I_{DQ} = 290 mA, (Pulsed: PW = 100 µs, DC = 10 %), T_{BASE} = 85°C, V_D = 28 V, I_{D_Drive} = 3.2 A P_{IN} = 20 dBm, P_{OUT} = 45.6 dBm, P_{DISS} = 52 W	0.788	°C/W
Channel Temperature (T_{CH}) (under RF drive)		126	°C

Notes:
1. Thermal resistance measured to back of package.
2. Refer to the following document: GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates

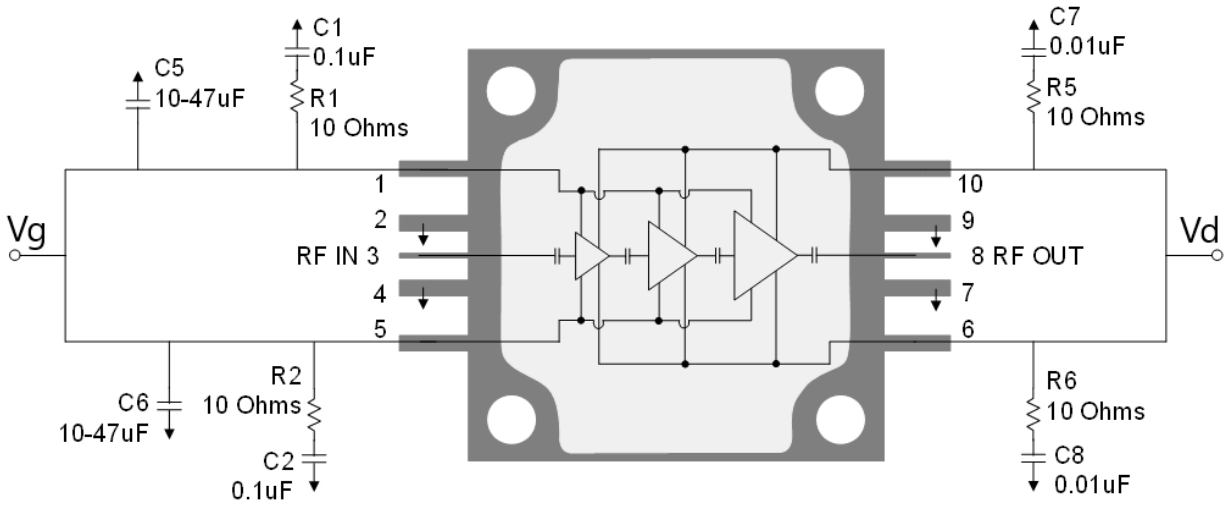
Power Dissipation and Maximum Gate Current







Applications Information and Pin Layout



Bias Up Procedure

1. Set I_D limit to 3.5 A, I_G limit to 25 mA
2. Apply −5 V to V_G
3. Apply +28 V to V_D; ensure I_{DQ} is approx. 0 mA
4. Adjust V_G until I_{DQ} = 290 mA (V_G ~ −2.7 V Typ.).
5. Turn on RF supply

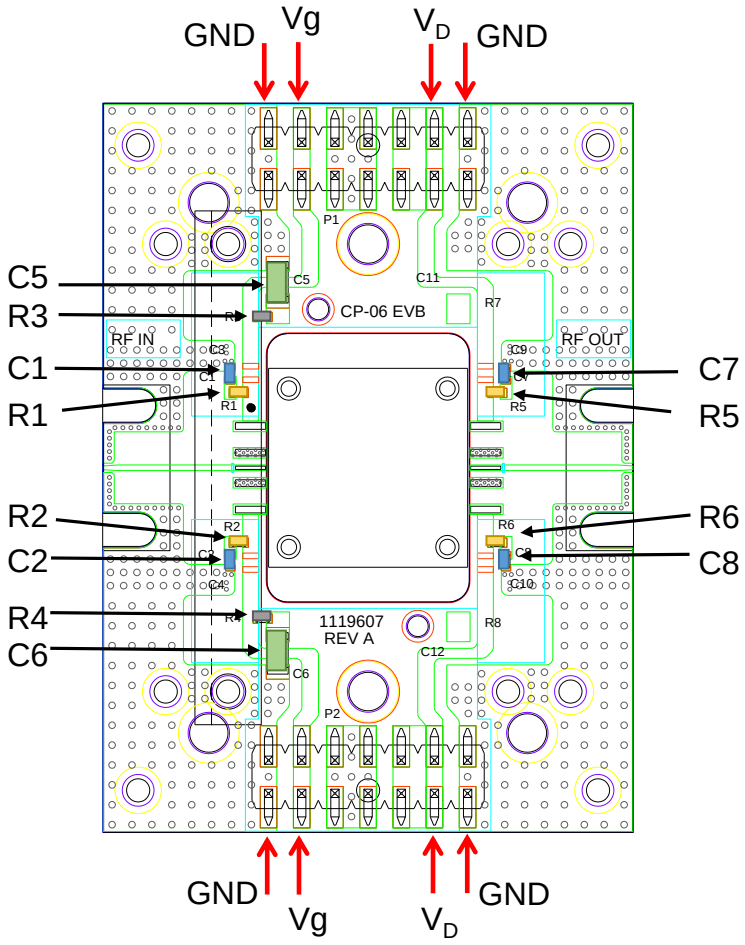
Bias Down Procedure

1. Turn off RF supply
2. Reduce V_G to −5 V; ensure I_{DQ} is approx. 0 mA
3. Set V_D to 0 V
4. Turn off V_D supply
5. Turn off V_G supply

Pin Description

Pad No.	Symbol	Description
1, 5	V_G	Gate Voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.
3	RF_{IN}	Output; matched to 50 Ω; DC blocked
2, 4, 7, 9	GND	Must be grounded on the PCB.
6, 10	V_D	Drain voltage; Bias network is required; must be biased from both sides; see recommended Application Information above.
8	RF_{OUT}	Input; matched to 50 Ω; DC blocked

Evaluation Board (EVB)



NOTES:

(1) Both Top and Bottom Vd and Vg must be biased.

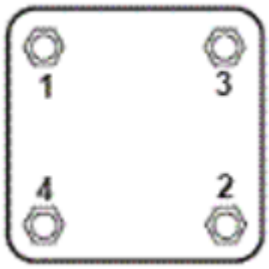
(2) PCB is made from Rogers 4003C dielectric, 0.008 inch thick. 0.5 oz. copper both sides.

Bill of Materials

Reference Des.	Value	Description	Manuf.	Part Number
C1, C2	0.1 uF	Cap, 0402, 50 V, 10%, X7R	Various	
C5, C6	10-47 uF	Cap, 1206, 50 V, 20%, X5R (10 V is OK)	Various	
C7, C8	0.01 uF	Cap, 0402, 50V, 10%, X7R	Various	
R1, R2, R5, R6	10 Ω	Res, 0402, 50V, 5%	Various	
R3, R4	0 Ω	Res, 0402, jumper required for the above EVB design	Various	

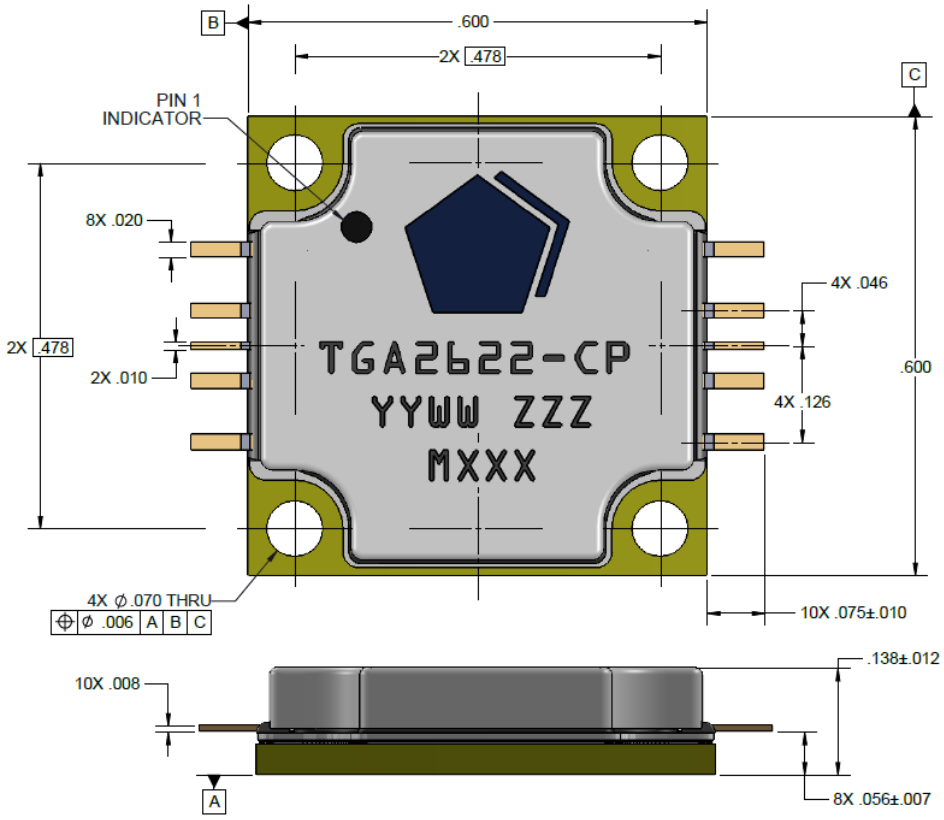
Assembly Notes

1. Carefully clean the PC board and package leads with alcohol. Allow it to dry fully.
2. To improve the thermal and RF performance, Qorvo recommends attaching a heat sink to the bottom of the PCB and apply thermal compound (Arctic Silver 5 recommended) or 4 mil indium shim between the heat sink and the package.
3. (The following is for *information only*. There are many variables in a second level assembly that Qorvo does not control, so Qorvo does not recommend an absolute torque value.) Use screws to attach the component to the heat sink. A suggested torque value is 16 in-oz. for a 0-80 screw. Start with screws finger tight, then torque to 8 in-oz., then torque to final value. Use the following tightening pattern:



4. Apply no-flux solder to each pin of the TGA2622-CP. The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. The use of no-clean solder to avoid washing after soldering is recommended.

Mechanical Information



Units: inches
Tolerances: unless specified
x.xx = ± 0.01
x.xxx = ± 0.005
Materials:
Base: Copper
Lid: Plastic
All metalized features are gold plated
Part is epoxy sealed
Marking:
2622: Part number
YY: Part Assembly year
WW: Part Assembly week
ZZZ: Serial Number
MXXX: Batch ID

Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	1B	ESDA / JEDEC JS-001-2014
ESD – Charged Device Model (CDM)	C1	ESDA / JEDEC JS-002-2014
MSL – Moisture Sensitivity Level	N/A	

Caution!
ESD-Sensitive Device

Solderability

The component leads should be manually soldered, and the package cannot be subjected to conventional reflow processes. Soldering of the component leads is compatible with the latest version of J-STD-020, lead-free solder, 260 °C. The use of no-clean solder to avoid washing after soldering is recommended.

RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU. This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A ($C_{15}H_{12}Br_4O_2$) Free
- PFOS Free
- SVHC Free

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

Web: www.qorvo.com

Tel: 1-844-890-8163

Email: customer.support@qorvo.com

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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

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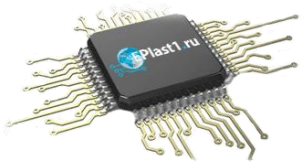
- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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